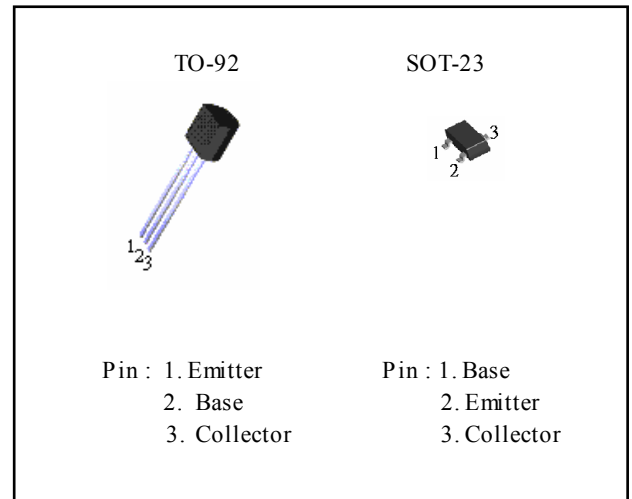


## NPN Epitaxial Silicon Transistor

**1W OUTPUT AMPLIFIER OF POTABLE  
RADIOS IN CLASS B PUSH-PULL OPERATION**

- High total power dissipation( $P_T=625mW$ )
- High collector Current ( $I_C=500mA$ )
- Complementary to PJ2N9012
- Excellent  $h_{EF}$  Linearity


**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )**

Rating	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	40	V
Collector Emitter Voltage	$V_{CEO}$	20	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	500	A
Collector Dissipation	$P_C$	625	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 ~150	$^\circ C$

**ORDERING INFORMATION**

Device	Operating Temperature	Package
PJ2N9013CT	-20 $^\circ C$ ~+85 $^\circ C$	TO-92
PJ2N9013CX		SOT-23

**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )**

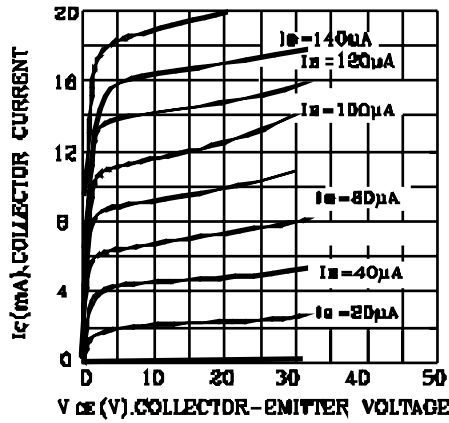
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=1mA, I_B=0$	20			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=25V, I_E=0$			100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=3V, I_C=0$			100	nA
DC Current Gain	$h_{FE1}$	$V_{EB}=1V, I_C=50mA$	64	120	202	
	$h_{FE2}$	$V_{EB}=1V, I_C=500mA$	40	90		
Collector- Base Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		0.16	0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$		0.91	1.2	V
Base-Emitter On Voltage	$V_{BE(ON)}$	$V_{CE}=1V, I_C=10mA$	0.6	0.67	0.7	V

 **$h_{EF}$  CLASSIFICATION**

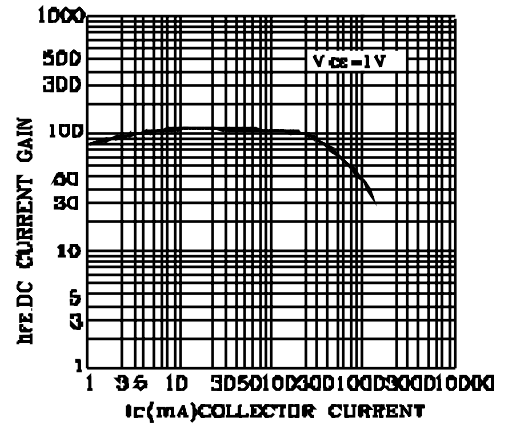
Classification	D	E	F	G	H
$h_{EF}$	64-91	78-112	96-135	112-166	144-202

**NPN Epitaxial Silicon Transistor**

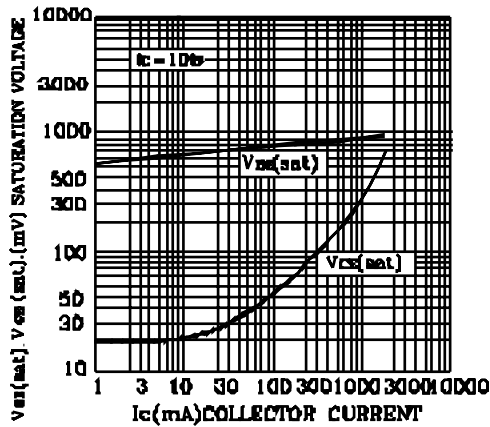
**STATIC CHARACTERISTIC**



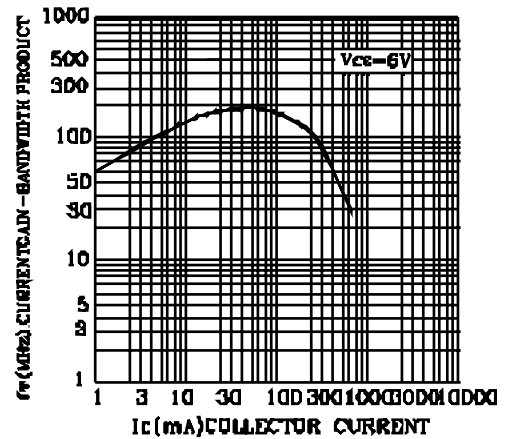
**DC CURRENT GAIN**



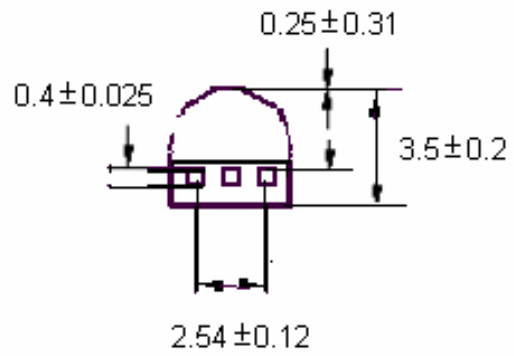
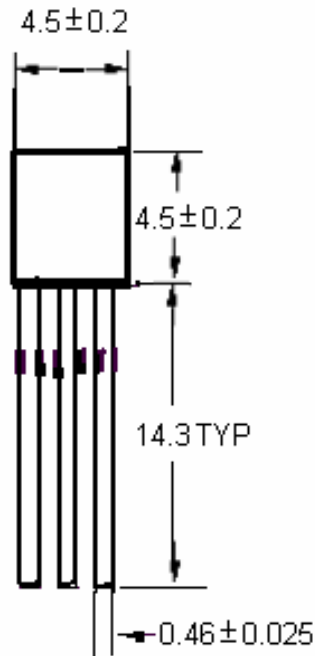
**BASE-EMITTER SATURATION VOLTAGE  
COLLECTOR-EMITTER SATURATION VOLTAGE**



**CURRENT GAIN-BANDWIDTH PRODUCT**



**TO-92 Unit:mm**



**SOT-23 Unit:mm**

